




Power MOSFETS


DATASHEET

LM30190DAI8A

N-Channel
Enhancement Mode MOSFET

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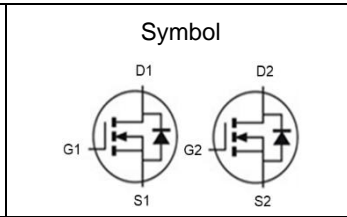
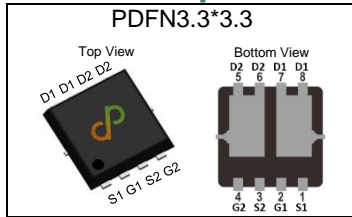


Quality Management Systems

ISO 9001:2015 Certificate

N-Channel Enhancement Mode MOSFET

Pin Description



Ordering Information

Symbol	N-Channel	Unit
V_{DSS}	30	V
$R_{DS(ON)-Max}$	18	mΩ
I_D	16	A

Feature

- Fast switching speed
- Reliable and Rugged
- ROHS Compliant & Halogen-Free
- 100% UIS Tested

Applications

- Portable Equipment
- Battery Powered System

Ordering Information

Orderable Part Number	Package Type	Form	Shipping	Marking
LM30190DAI8A	PDFN3.3*3.3 (Dual)	Tape & Reel	5000 / Tape & Reel	30190 □□□□□C

Absolute Maximum Ratings (T_J=25°C Unless Otherwise Noted)

Symbol	Parameter	N-Channel	Unit	
V_{DSS}	Drain-Source Voltage	30	V	
V_{GSS}	Gate-Source Voltage	±20		
T_J	Maximum Junction Temperature	150	°C	
T_{STG}	Storage Temperature Range	-55 to 150	°C	
$I_{DM}^{①}$	Pulse Drain Current Tested	$T_c=25^\circ\text{C}$	28	A
I_D	Continuous Drain Current	$T_c=25^\circ\text{C}$	16	A
		$T_c=100^\circ\text{C}$	10	
P_D	Maximum Power Dissipation	$T_c=25^\circ\text{C}$	7.8	W
		$T_c=100^\circ\text{C}$	3.1	
$I_{AS}^{②}$	Avalanche Current, Single pulse	L=0.1mH	12	A
$E_{AS}^{②}$	Avalanche Energy, Single pulse	L=0.1mH	7.2	mJ

Thermal Characteristics

Symbol	Parameter	Rating	Unit	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	Steady State	16	°C/W
$R_{\theta JA}^{③}$	Thermal Resistance-Junction to Ambient	Steady State	100	°C/W

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150°C

Note ③ : Surface Mounted on 1in² FR-4 board with 1oz.

N-Channel Electrical Characteristics (T_J=25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250uA	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V	-	-	1	uA
V_{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250uA	1	1.5	2	V
I_{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R_{DS(ON)}^④	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =10A	-	15	18	mΩ
		V _{GS} =4.5V, I _{DS} =8A	-	18	24	
g_{fs}	Forward Transconductance	V _{DS} =5V, I _{DS} =5A	-	8	-	S
Dynamic Characteristics[®]						
R_G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, Freq.=1MHz	-	3	-	Ω
C_{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Freq.=1MHz	-	500	-	pF
C_{oss}	Output Capacitance					
C_{riss}	Reverse Transfer Capacitance					
t_{d(ON)}	Turn-on Delay Time	V _{GS} =10V, V _{DS} =15V, I _D =1A, R _{GEN} =6Ω	-	3.1	-	nS
t_r	Turn-on Rise Time					
t_{d(OFF)}	Turn-off Delay Time					
t_f	Turn-off Fall Time					
Q_g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =15V, I _D =10A	-	8.5	-	nC
Q_g	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =10A	-	15.2	-	
Q_{gs}	Gate-Source Charge		-	1.3	-	
Q_{gd}	Gate-Drain Charge		-	4.7	-	
Source-Drain Characteristics						
V_{SD}^④	Diode Forward Voltage	I _{SD} =5A, V _{GS} =0V	-	0.7	1.1	V
t_{rr}	Reverse Recovery Time	I _F =1A, V _R =15V	-	9	-	nS
Q_{rr}	Reverse Recovery Charge	dI _F /dt=100A/μs	-	3	-	nC

Note ④ : Pulse test (pulse width≤300us, duty cycle≤2%).

Note ⑤ : Guaranteed by design, not subject to production testing.

N-Channel Typical Characteristics

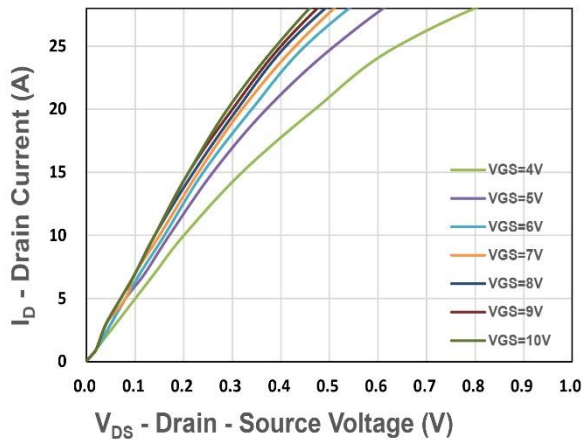


Figure 1. Output Characteristics

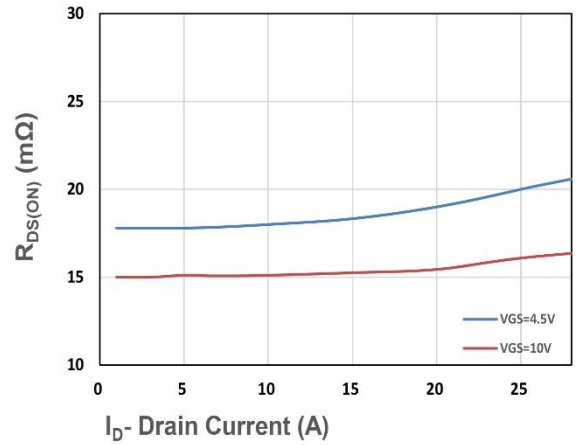


Figure 2. On-Resistance vs. ID

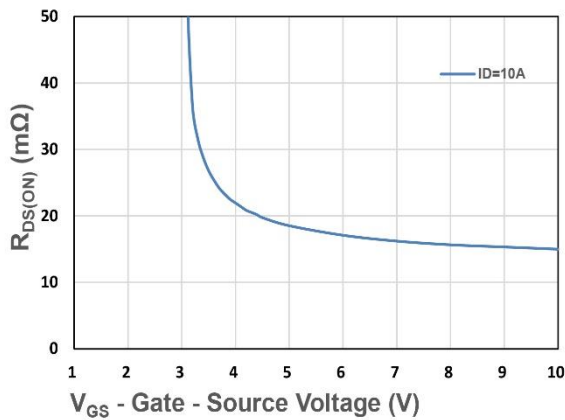


Figure 3. On-Resistance vs. VGS

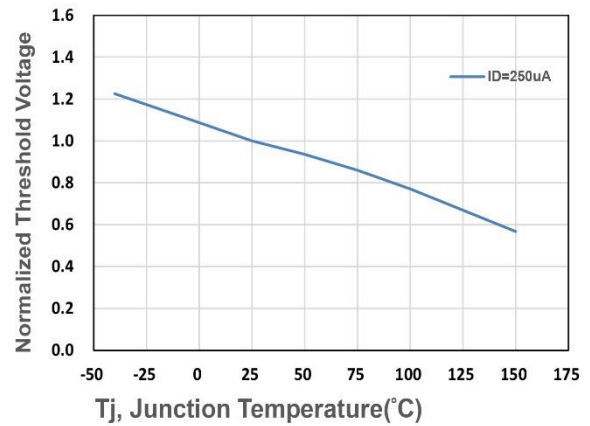


Figure 4. Gate Threshold Voltage

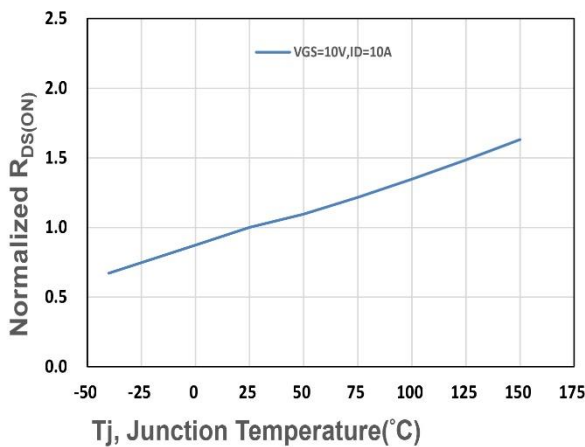


Figure 5. Drain-Source On Resistance

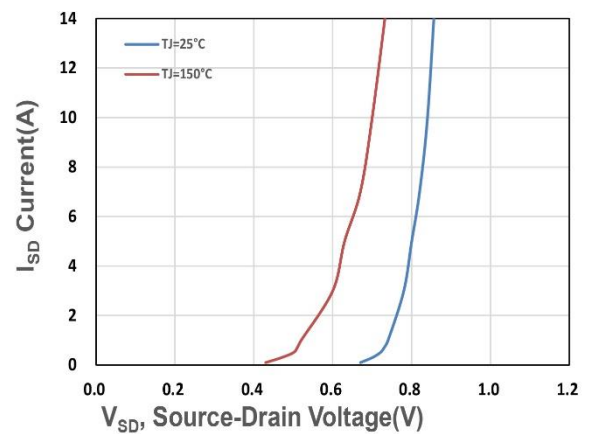
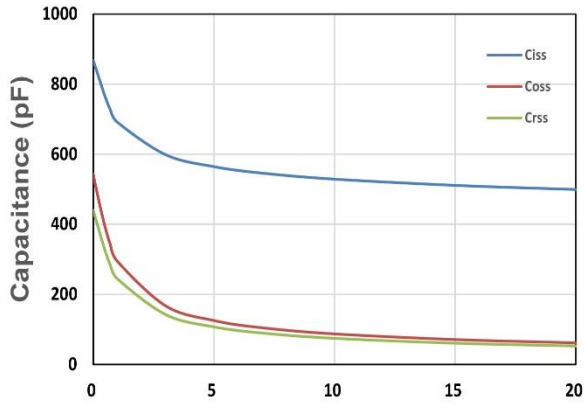
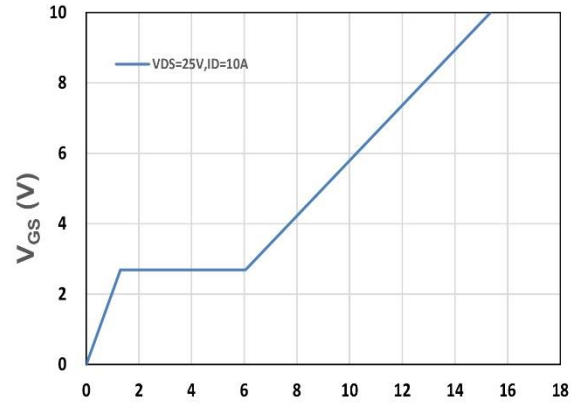


Figure 6. Source-Drain Diode Forward



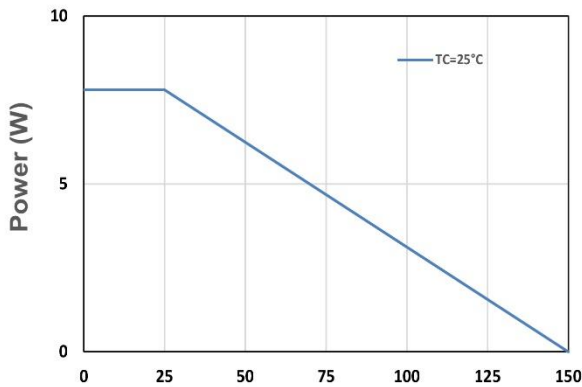
V_{DS} - Drain - Source Voltage (V)

Figure 7. Capacitance



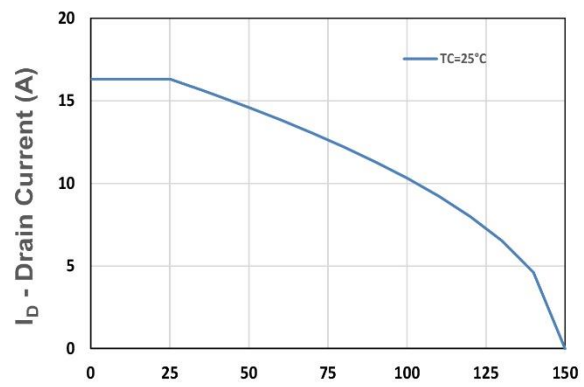
Q_g , Total Gate Charge (nC)

Figure 8. Gate Charge Characteristics



T_c - Junction Temperature (°C)

Figure 9. Power Dissipation



T_c - Junction Temperature (°C)

Figure 10. Drain Current

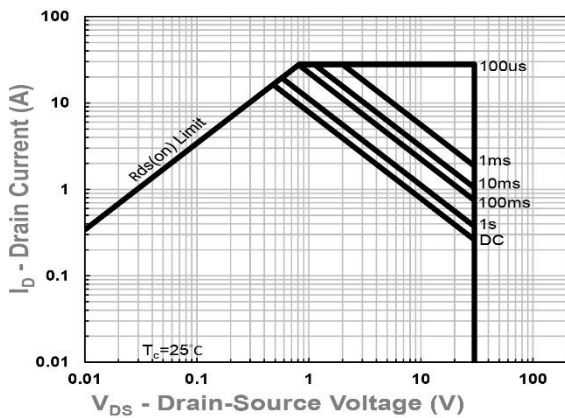


Figure 11. Safe Operating Area

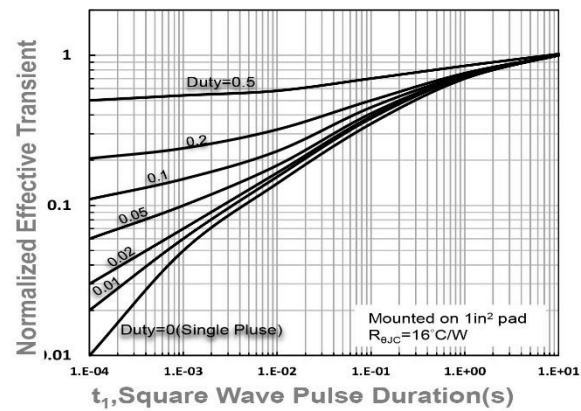


Figure 12. $R_{\theta JC}$ Transient Thermal Impedance